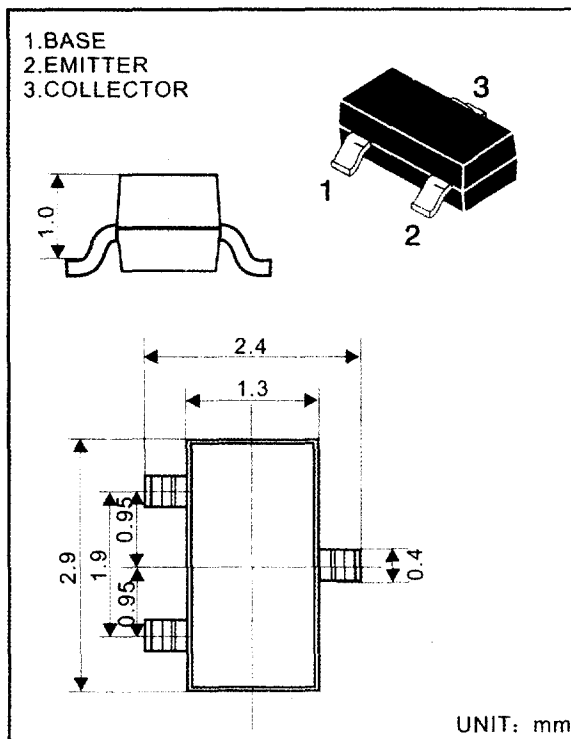


# SOT-23 Plastic-Encapsulate Transistors

## BC856A/BLT1,857A/BLT1,858A/B/CLT1 TRANSISTOR (PNP)



### FEATURES

#### Power dissipation

$P_{CM}$ : 0.3 W ( $T_{amb}=25^{\circ}C$ )

#### Collector current

$I_{CM}$ : -0.1 A

#### Collector-base voltage

$V_{(BR)CBO}$ : BC856:-80V BC857:-50V BC858:-30V

#### Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$

### ELECTRICAL CHARACTERISTICS

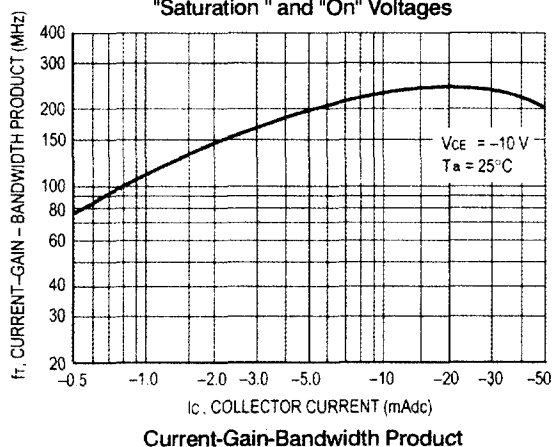
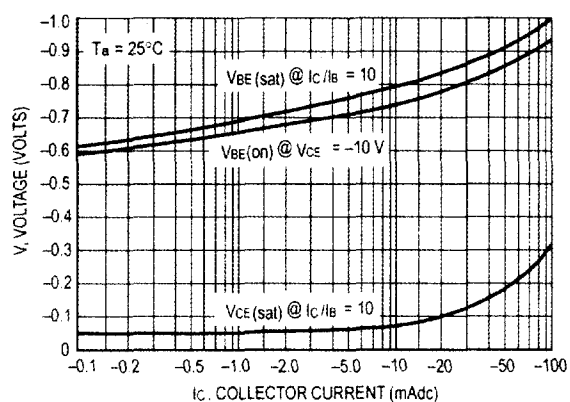
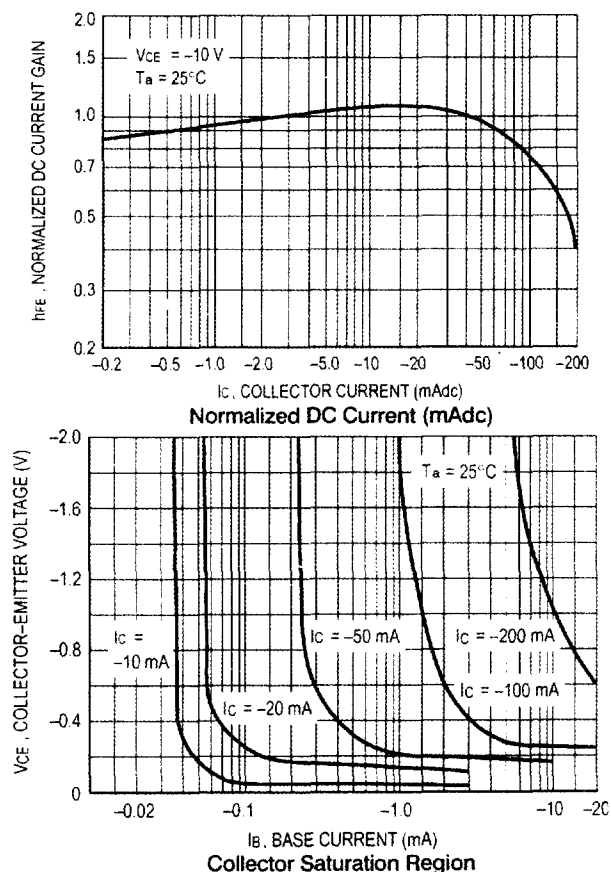
( $T_{amp}=25^{\circ}C$  unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10 \mu A, I_E = 0$	-80 -50 -30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10 mA, I_B = 0$	-65 -45 -30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1 \mu A, I_B = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -70V, I_E = 0$ $V_{CB} = -45V, I_E = 0$ $V_{CB} = -25V, I_E = 0$			-0.1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE} = -60V, I_B = 0$ $V_{CE} = -40V, I_B = 0$ $V_{CE} = -25V, I_B = 0$			-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$			-0.1	$\mu A$
DC current gain	BC856A, BC857A, BC858A	$V_{CE} = -5V, I_C = -2mA$	125		250	
	BC856B, BC857B, BC858B		220		475	
	BC858C		420		800	
Collector-emitter saturation voltage	$V_{CEsat}$	$I_C = -100mA, I_B = -5mA$			-0.5	V
Base-emitter saturation voltage	$V_{BEsat}$	$I_C = -100mA, I_B = -5mA$			-1	V
Transition frequency	$f_T$	$V_{CE} = -5V, I_C = -10mA, f = 100MHz$	100			MHz

DEVICE MARKING : BC856A=3A, BC856A=3B, BC857A=3E, BC857B=3F, BC858=3J, BC858B=3K, BC858C=3L

# Typical Characteristics BC856A/BLT1,BC857A/BLT1,BC858A/B/CLT1

## BC857,BC858



## BC856

